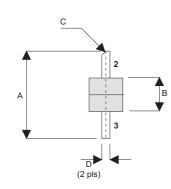
TetraFET

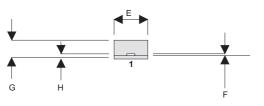
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ROHS COMPLIANT METAL GATE RF SILICON FET

MECHANICAL DATA





DP

PIN 1 SOURCE

PIN 3 GATE

Н

0.64

DRAIN

PIN 2

DIM	mm	Tol.	Inches	Tol.
Α	16.51	0.25	0.650	0.010
В	6.35	0.13	0.250	0.005
С	45°	5°	45°	5°
D	1.52	0.13	0.060	0.005
Е	6.35	0.13	0.250	0.005
F	0.13	0.03	0.005	0.001
G	3.56	0.51	0.140	0.020

0.13

0.024

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 5W - 28V - 1GHz SINGLE ENDED

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND **APPLICATIONS**
- LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 13 dB MINIMUM

APPLICATIONS

 VHF/UHF COMMUNICATIONS from DC to 1 GHz

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

0.005

P _D	Power Dissipation	29W
BV _{DSS}	Drain – Source Breakdown Voltage	65V
BV _{GSS}	Gate – Source Breakdown Voltage	±20V
I _{D(sat)}	Drain Current	2A
T _{stg}	Storage Temperature	–65 to 150°C
Tj	Maximum Operating Junction Temperature	200°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

	Parameter	Test Conditions			Min.	Тур.	Max.	Unit
B\/	Drain-Source	V _{GS} = 0	I _D = 10mA	10mA	65			V
BV _{DSS}	Breakdown Voltage	VGS – 0		IUIIIA				Ň
	Zero Gate Voltage	V = = = 29V	V V _{GS} = 0			2	mA	
IDSS	Drain Current	V _{DS} = 28V		= 0			Z	IIIA
I _{GSS}	Gate Leakage Current	$V_{GS} = 20V$	V _{DS}	= 0			1	μΑ
V _{GS(th)}	Gate Threshold Voltage*	I _D = 10mA	V _{DS}	= V _{GS}	1		7	V
9 _{fs}	Forward Transconductance*	V _{DS} = 10V	I _D =	0.4A	0.36			S
G _{PS}	Common Source Power Gain	$P_0 = 5W$			13			dB
η	Drain Efficiency	V _{DS} = 28V	I _{DQ}	= 0.2A	40			%
VSWR	Load Mismatch Tolerance	f = 1GHz			20:1			—
C _{iss}	Input Capacitance	$V_{DS} = 0$	$V_{GS} = -5V$	f = 1MHz			20	pF
C _{oss}	Output Capacitance	V _{DS} = 28V	$V_{GS} = 0$	f = 1MHz			11	pF
C _{rss}	Reverse Transfer Capacitance	V _{DS} = 28V	$V_{GS} = 0$	f = 1MHz			1	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 6.0°C / W
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